

## RF power transistor the LdmoST family

## **Technical Literature**

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LABEL	USER FUNCTION	DATE
Camilleri Evelina	Document Controller	27-May-2013



# SD57030

# RF power transistor the LdmoST family

#### **Features**

- Excellent thermal stability
- Common source configuration
- P<sub>OUT</sub> = 30W with 13dB gain @ 945MHz
- BeO free package
- Internal input matching
- In compliance with the 2002/95/EC european directive

# **Description**

The SD57030 is a common source N-channel enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The SD57030 is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for base station applications requiring high linearity.

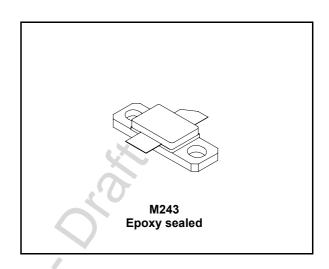


Figure 1. Pin connection

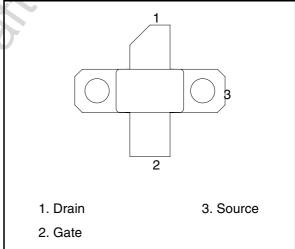


Table 1. Device summary

Order code	Package	Branding
SD57030	M243	SD57030

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SD57030 Electrical data

# 1 Electrical data

# 1.1 Maximum ratings

Table 1. Absolute maximum ratings  $(T_{CASE} = 25^{\circ}C)$ 

Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-Source voltage	65	V
V <sub>DGR</sub>	Drain-Gate voltage ( $R_{GS} = 1 \text{ M}\Omega$ )	65	V
V <sub>GS</sub>	Gate-Source voltage	+ 20	V
I <sub>D</sub>	Drain current	4	Α
P <sub>DISS</sub>	Power dissipation (@ Tc = 70°C)	74	W
Tj	Max. operating junction temperature	200	°C
T <sub>STG</sub>	Storage temperature	-65 to + 200	°C

## 1.2 Thermal data

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJC}$	Junction - case thermal resistance	1.75	°C/W



Electrical characteristics SD57030

# 2 Electrical characteristics

 $T_{CASE} = +25$  °C

#### 2.1 Static

Table 3. Static (per section)

Symbol		Test conditions	Min	Тур	Max	Unit	
V <sub>(BR)DSS</sub>	$V_{GS} = 0 V$	$I_{DS} = 10 \text{ mA}$		65			V
I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 28 V				1	μΑ
I <sub>GSS</sub>	V <sub>GS</sub> = 20 V	$V_{DS} = 0 V$				1	μΑ
V <sub>GS(Q)</sub>	V <sub>DS</sub> = 28 V	$I_D = 50 \text{ mA}$		2.0		5.0	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V	$I_D = 3 A$			1.3		V
G <sub>FS</sub>	V <sub>DS</sub> = 10 V	I <sub>D</sub> = 3 A			1.8		mho
C <sub>ISS</sub> <sup>(1)</sup>	$V_{GS} = 0 V$	V <sub>DS</sub> = 28 V	f = 1 MHz		58		pF
Coss	$V_{GS} = 0 V$	V <sub>DS</sub> = 28 V	f = 1 MHz		34		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 28 V	f = 1 MHz		2.7		pF

<sup>1.</sup> Includes Internal Input Moscap.

# 2.2 Dynamic

Table 4. Dynamic

Symbol	Test conditions	Min	Тур	Max	Unit
P <sub>OUT</sub>	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 50 \text{ mA}$ $f = 945 \text{ MHz}$	30			W
G <sub>PS</sub>	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 50 \text{ mA } P_{OUT} = 30 \text{ W}$ $f = 945 \text{ MHz}$	13	15		dB
h <sub>D</sub>	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 50 \text{ mA}$ $P_{OUT} = 30 \text{ W}$ $f = 945 \text{ MHz}$	50	60		%
Load mismatch	$V_{DD} = 28~V~~I_{DQ} = 50~mA~~P_{OUT} = 28~W~~f = 945~MHz$ All phase angles	10:1			VSWR

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# 3 Typical performance (CW)

Figure 2. Output power vs input power

Figure 3. Power gain and efficiency vs output power

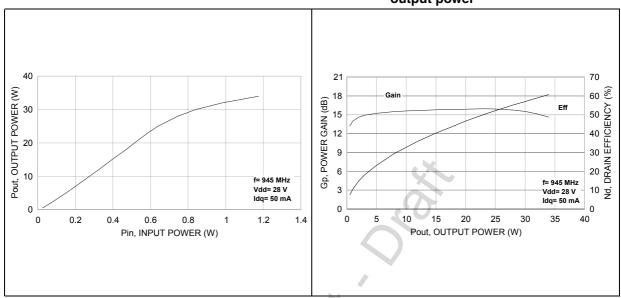
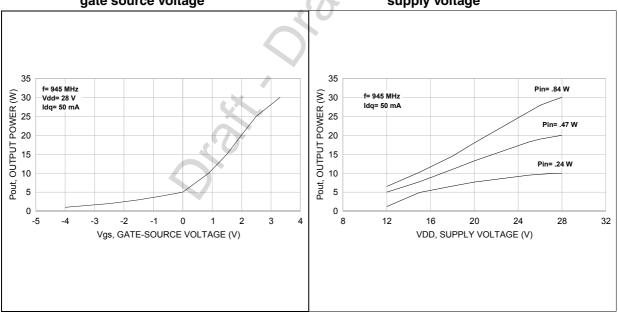


Figure 4. Output power vs gate source voltage

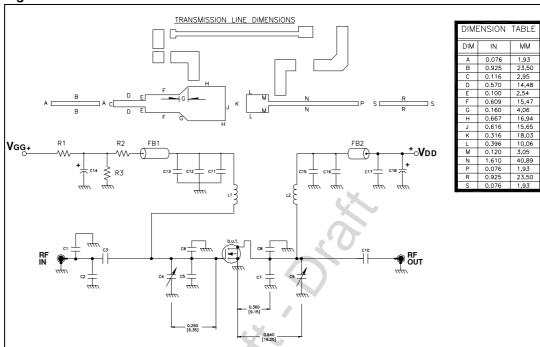
Figure 5. Output power vs supply voltage



Test circuit SD57030

## 4 Test circuit

Figure 6. Test circuit schematic



- 1 Dimensions at component symbols are reference for component placement.
- 2 Gap between ground & transmission line = 0.056 [1.42] +0.002 [0.05] -0.000 [0.00] typ.
- 3 Dimensions of input and output component from edge of transmission lines.

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SD57030 Test circuit

Table 5. Test circuit component part list

Component	Description
C19	200 μF / 63V ALLUMINIUM ELECTROLYTIC RADIAL LEAD CAPACITOR
C18, C14	0.1 μF / 500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C17	100 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C16, C12, C11,C1	47 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C15	10 μF / 50V ALUMINIUM ELECTROLYTIC RADIAL LEAD CAPACITOR
C13	100 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C9, C2	0.8-8.0 pF GIGA TRIM VARIABLE CAPACITOR
C8	6.2 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C7, C6, C5 ,C4	10 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C3	3 pF ATC 100B SURFACE MOUNT CERAMIC CHIP CAPACITOR
R3	120 0-IM, 2W SURFACE MOUNT CERAMIC CHIP CAPACITOR
R2	4.7 M OHM 1W SURFACE MOUNT CERAMIC CHIP CAPACITOR
R1	18 K OHM, 1W SURFACE MOUNT CERAMIC CHIP CAPACITOR
FB2, FB1	SHIELD BEAD SURFACE MOUNT EMI
L2, L1	INDUCTOR, 5 TURNS AIR WOUND #22AWG, ID=0.059[1.49], NYLON COATED MAGNET WIRE
PCB	WOVEN FIBERGLASS REINFORCED PTFE 0.080" THK, $\epsilon$ r=2.55, 2 Oz EDCu BOTH SIDE



**Text circuit layout** SD57030

#### **Text circuit layout** 5

Figure 7. **Test fixture** 

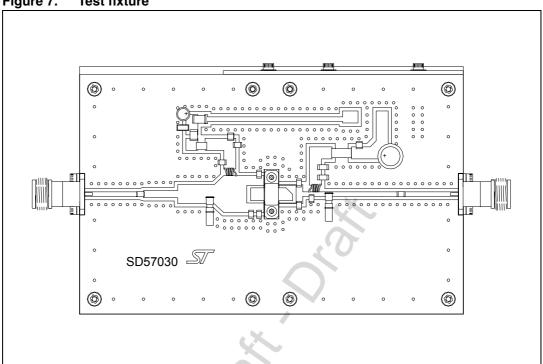
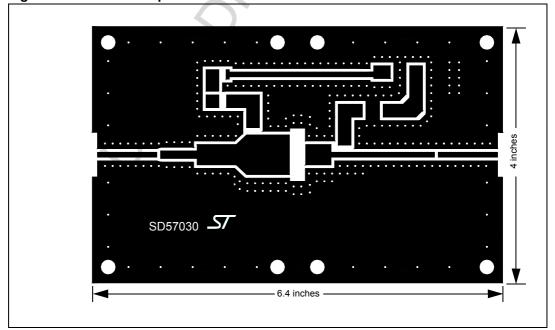


Figure 8. Test circuit photomaster



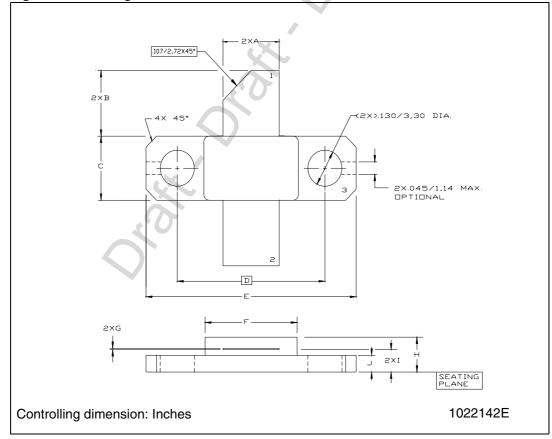
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# 6 Package mechanical data

Table 6. M243 (.230 x .360 2L N/HERM W/FLG) mechanical data

Dim.	mm.				Inch	
	Min	Тур	Max	Min	Тур	Max
Α	5.21		5.72	0.205		0.225
В	5.46		6.48	0.215		0.255
С	5.59		6.10	0.220		0.240
D		14.27			0.562	
Е	20.07		20.57	0.790		0.810
F	8.89		9.40	0.350		0.370
G	0.10		0.15	0.004		0.006
Н	3.18		4.45	0.125		0.175
I	1.83		2.24	0.072		0.088
J	1.27		1.78	0.050		0.070

Figure 9. Package dimensions





Revision history SD57030

# 7 Revision history

Table 7. Document revision history

Date	Revision	Changes
24-Mar-2003	5	First Issue.
11-Jul-2007	6	Document reformatted, added lead free info
24-Aug-2007	7	Cover page title updated



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